East Search In Paper No. 17

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	11	"5518962" and (nitride sin si3n4 "si.sub.3n.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 10:21
S2	23	("4872947" | "5271972" | "5356722" | "5376590" | "5387546" | "5424253" | "5459105" | "5518962" | "5525551").PN. OR ("5563104"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/05/05 11:12
S3	22	("5021358" | "5132241" | "5225357" | "5244821" | "5266510" | "5405791" | "5407847" | "5434096" | "5460993" | "5502009" | "5504031" | "5563104" | "5599726" | "5707896").PN. OR ("5811343").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/05/05 11:40
S4	4534	gate with silicon adj oxide with silicon adj nitride	US-PGPUB; USPAT; USOCR	OR	ON	2004/05/05 11:41
S5	101	gate with protective with silicon adj oxide with silicon adj nitride	US-PGPUB; USPAT; USOCR	OR	ON	2004/05/05 14:46
S6	6	("6121098" "5679606" "5811343" "200400412213" "20020030234" "6642585" "6117767").pn.	US-PGPUB; USPAT; USOCR	OR	ON	2004/05/05 12:06
S7	1	"20040041213".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2004/05/05 12:07
S8	5	("6121098" "5679606" "5811343" "6642585" "6117767").pn.	US-PGPUB; USPAT; USOCR	OR	ON	2004/05/05 12:07
S9	0	split adj gate with protective with silicon adj oxide with silicon adj nitride	US-PGPUB; USPAT; USOCR	OR	ON	2004/05/05 14:46
S10	0	split adj gate same protective with silicon adj oxide with silicon adj nitride	US-PGPUB; USPAT; USOCR	OR	ON	2004/05/05 14:47
S11	55	split adj gate same silicon adj oxide with silicon adj nitride	US-PGPUB; USPAT; USOCR	OR	ON	2004/05/05 17:50

S12	0	split adj gate same protective with silicon adj oxide with silicon adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 14:47
S13	62	split adj gate same silicon adj oxide with silicon adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 15:03
S14	2	"5198380".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 14:58
S15	2	"4561004".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 14:58
S16	58	split adj gate and control adj gate with (sio sio2 "sio.sub.2" silicon adj oxide) with (sin si3n4 "si.sub.3n.sub.4" silicon adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 15:22
S17	0	split adj gate and interdielectric with (sio sio2 "sio.sub.2" silicon adj oxide) with (sin si3n4 "si.sub.3n.sub.4" silicon adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 17:09
S18	5	split adj gate and interlayer with (sio sio2 "sio.sub.2" silicon adj oxide) with (sin si3n4 "si.sub.3n.sub.4" silicon adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 15:24
S19	0	split adj gate and intermetal with (sio sio2 "sio.sub.2" silicon adj oxide) with (sin si3n4 "si.sub.3n.sub.4" silicon adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 15:25

S20	7	split adj gate and protective with (sio sio2 "sio.sub.2" silicon adj oxide) with (sin si3n4 "si.sub.3n.sub.4" silicon adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 15:26
S21	199	nonvolatile and (interlevel interdielectric intermetal interlayer) with (sio sio2 "sio.sub.2" silicon adj oxide) with (sin si3n4 "si.sub.3n.sub.4" silicon adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 15:53
S22	11	S21 and split	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 15:27
S23	4	("20010002713" "6673672").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 15:53
S24	13	interdielectric with (sio sio2 "sio.sub.2" silicon adj oxide) with (sin si3n4 "si.sub.3n.sub.4" silicon adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 17:11
S25	241	(interinsulating interdielectric interlevel intermetal) with (sio sio2 "sio.sub.2" silicon adj oxide) with (sin si3n4 "si.sub.3n.sub.4" silicon adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 17:12
S26	31	(interinsulating interdielectric interlevel intermetal) with first with second with (sio sio2 "sio.sub.2" silicon adj oxide) with (sin si3n4 "si.sub.3n.sub.4" silicon adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 17:18
S27	16	(interinsulating interdielectric interlevel intermetal) with combination with (sio sio2 "sio.sub.2" silicon adj oxide) with (sin si3n4 "si.sub.3n.sub.4" silicon adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 17:52

S28	2	"20010002713".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/05 17:52